

# **DESCRIPTION**

The HX2300A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications.

# **GENERAL FEATURES**

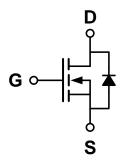
- ♦ High power and current handing capability
- ♦ Lead free product is acquired
- ♦ Surface mount package

## **APPLICATION**

- ♦ PWM applications
- ♦ Load switch

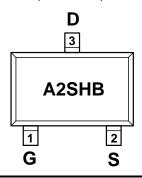
## **PACKAGE**

# **SCHEMATIC DIAGRAM**



# **PIN ASSIGNMENT**

SOT-23 (TOP VIEW)



## **ORDERING INFORMATION**

Part Number	Storage Temperature	Package	Marking	Devices Per Reel
HX2300A	-55°C to +150°C	SOT-23	A2SHB	3000

#### ABSOLUTE MAXIMUM RATINGS

## (T<sub>A</sub>=25℃ unless otherwise noted)

parameter		symbol	limit	unit	
Drain-source voltage	V <sub>DS</sub>	20	V		
Gate-source voltage	V <sub>GS</sub>	±12	V		
Continuous drain surrent /T 450 °C) 8	T <sub>A</sub> =25°C		2.5		
Continuous drain current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> =70°C	l <sub>D</sub>	2.0		
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	10	Α		
Continuous source current (diode conduction) a	Is	0.6			
Device discipation 2	T <sub>A</sub> =25°C	Б	0.71	10/	
Power dissipation <sup>a</sup>	T <sub>A</sub> =70°C	P <sub>D</sub>	0.46	W	
Operating junction and storage temperature rar	T <sub>J</sub> , T <sub>stg</sub>	-55—150	$^{\circ}$		

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# THERMAL CHARACTERISTICS

Parameter		Symbol	Тур	Max	Unit
Maximum junction to ambient 8	≤5 s	D	120	120 145	
Maximum junction-to-ambient <sup>a</sup>	Steady-State	$R_{ heta JA}$	140	175	°C/W
Maximum junction-to-foot	Steady-State	R <sub>θJC</sub>	62	78	

#### Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. Pulse width limited by maximum junction temperature

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit		
OFF Characteristics								
Drain-source breakdown voltage	BV <sub>DSS</sub>	SS V <sub>GS</sub> =0V, I <sub>D</sub> =250μA		-	-	V		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	μΑ		
Gate-body leakage	I <sub>GSS</sub>	GSS V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V		-	±100	nA		
	ON Characteristics							
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	0.5	0.65	1.0	V		
Due in account on atota register as 2	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.5A	-	46	60	mΩ		
Drain-source on-state resistance <sup>a</sup>		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1A		61	85			
Forward transconductance <sup>a</sup>	gfs	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	-	5	-	S		
	Dynamic C	Characteristics b	•					
Input capacitance	C <sub>ISS</sub>		-	180	-	pF		
Output capacitance	Coss	V <sub>DS</sub> =10V ,V <sub>GS</sub> =0V f=1.0MHz	-	38	-			
Reverse transfer capacitance	C <sub>RSS</sub>	1-1.01/11/12	-	20	-			
Switching Characteristics								
Turn-on delay time	t <sub>D(ON)</sub>	V <sub>DD</sub> =10V	-	8	-			
Rise time	tr	$R_L=3 \text{ ohm}$	-	7	-			
Turn-off delay time	t <sub>D(OFF)</sub>	V <sub>GEN</sub> =4.5V	-	30	-	ns		
Fall time	tf	R <sub>GEN</sub> =6ohm	-	7	-			
Total gate charge	Qg	V <sub>DS</sub> =10V	-	3.5	-			
Gate-source charge	Qgs	I <sub>D</sub> =2.5A	-	0.6	-	nC		
Gate-drain charge	Qgd	V <sub>GS</sub> =4.5V	-	0.45	-			
DRAIN-SOURCE DIODE CHARACTERISTICS								
Diode forward voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,Is=2.5A	-	0.76	1.16	V		

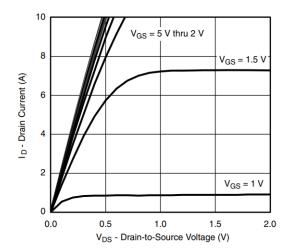
#### **Notes**

- a. Pulse test: Pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

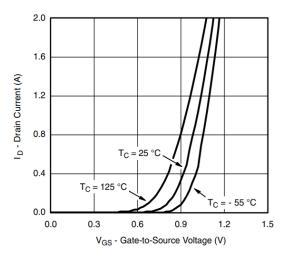
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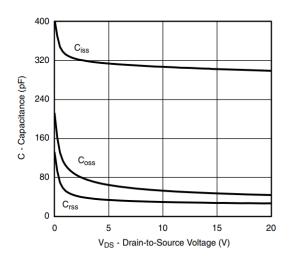
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



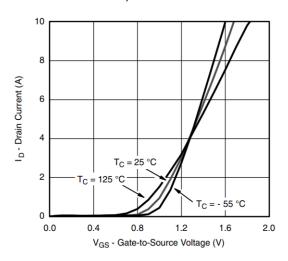
#### **Output Characteristics**



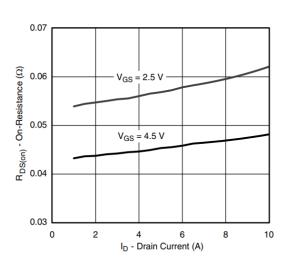
### **Transfer Characteristics**



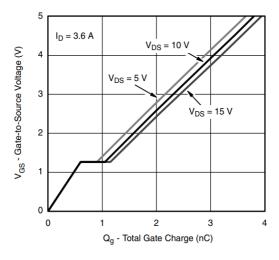
Capacitance



#### **Transfer Characteristics**



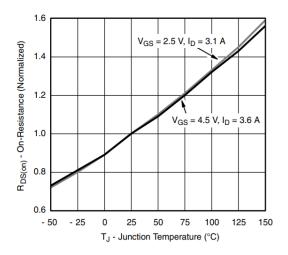
On-Resistance vs. Drain Current



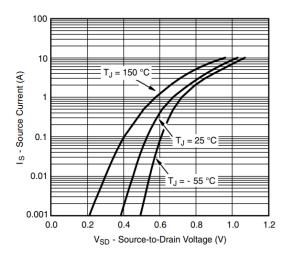
**Gate Charge** 

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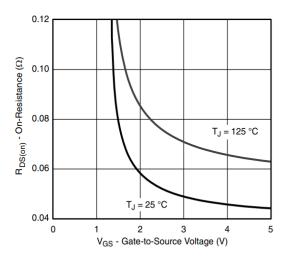




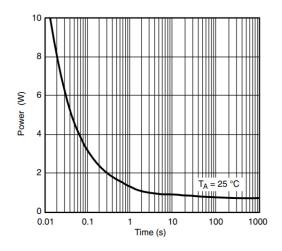
On-Resistance vs. Junction Temperature



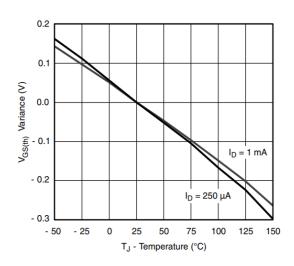
Source-Drain Diode Forward Voltage



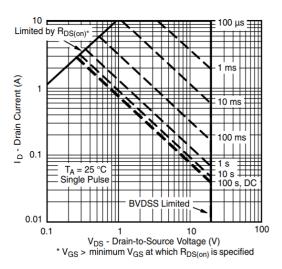
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power



Threshold Voltage



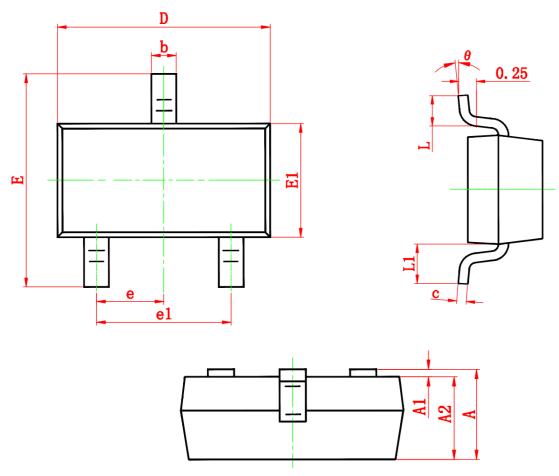
Safe Operating Area, Junction-to-Ambient

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# **PACKAGE INFORMATION**

# • SOT-23

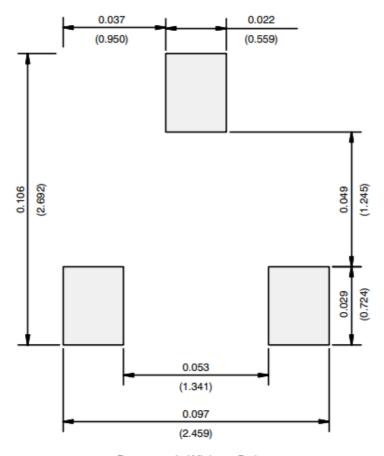


Complete	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	2.250	2.550	0.089	0.100	
E1	1.200	1.400	0.047	0.055	
е	0.950	TYP.	0.037 TYP.		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.500	0.012	0.020	
L1	0.550	0.550 REF.		)22 REF.	
θ	θ 0°		0°	8°	

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# **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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